

PSMN8R7-80PS

N-channel 80 V 8.7 mΩ standard level MOSFET in TO-220

Rev. 02 — 1 November 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

1.3 Applications

- DC-to-DC converters
- Motor control
- Load switching
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

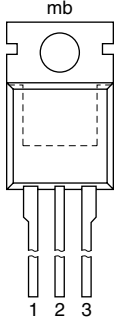
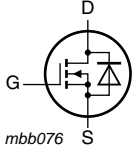
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	80	V
I_D	drain current	$T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see Figure 1	-	-	90	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C};$ see Figure 2	-	-	170	W
T_j	junction temperature		-55	-	175	°C
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 10\text{ A};$ $T_j = 100\text{ °C};$ see Figure 12	-	-	14	mΩ
		$V_{GS} = 10\text{ V}; I_D = 10\text{ A};$ $T_j = 25\text{ °C};$ see Figure 13	[1]	-	7.5	8.7
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 25\text{ A};$ $V_{DS} = 40\text{ V};$ see Figure 14 ;	-	11	-	nC
$Q_{G(tot)}$	total gate charge	see Figure 15	-	52	-	nC
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(init)} = 25\text{ °C};$ $I_D = 90\text{ A}; V_{sup} \leq 80\text{ V};$ $R_{GS} = 50\text{ Ω};$ unclamped	-	-	120	mJ

[1] Measured 3 mm from package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

SOT78 (TO-220AB)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN8R7-80PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	80	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	80	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see Figure 1	-	64	A
		V _{GS} = 10 V; T _{mb} = 25 °C; see Figure 1	-	90	A
I _{DM}	peak drain current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; see Figure 3	-	361	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	170	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
T _{slid(M)}	peak soldering temperature		-	260	°C
Source-drain diode					
I _S	source current	T _{mb} = 25 °C	-	90	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C	-	361	A
Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V _{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 90 A; V _{sup} ≤ 80 V; R _{GS} = 50 Ω; unclamped	-	120	mJ

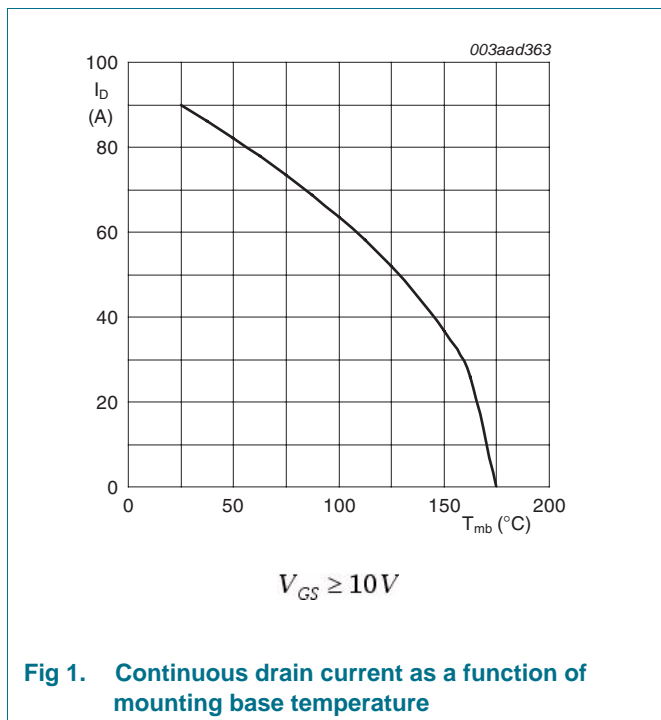


Fig 1. Continuous drain current as a function of mounting base temperature

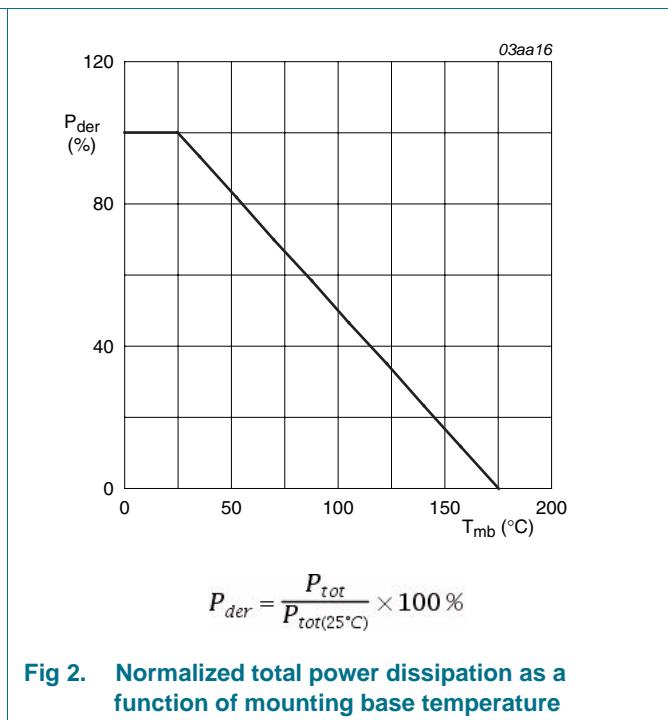


Fig 2. Normalized total power dissipation as a function of mounting base temperature

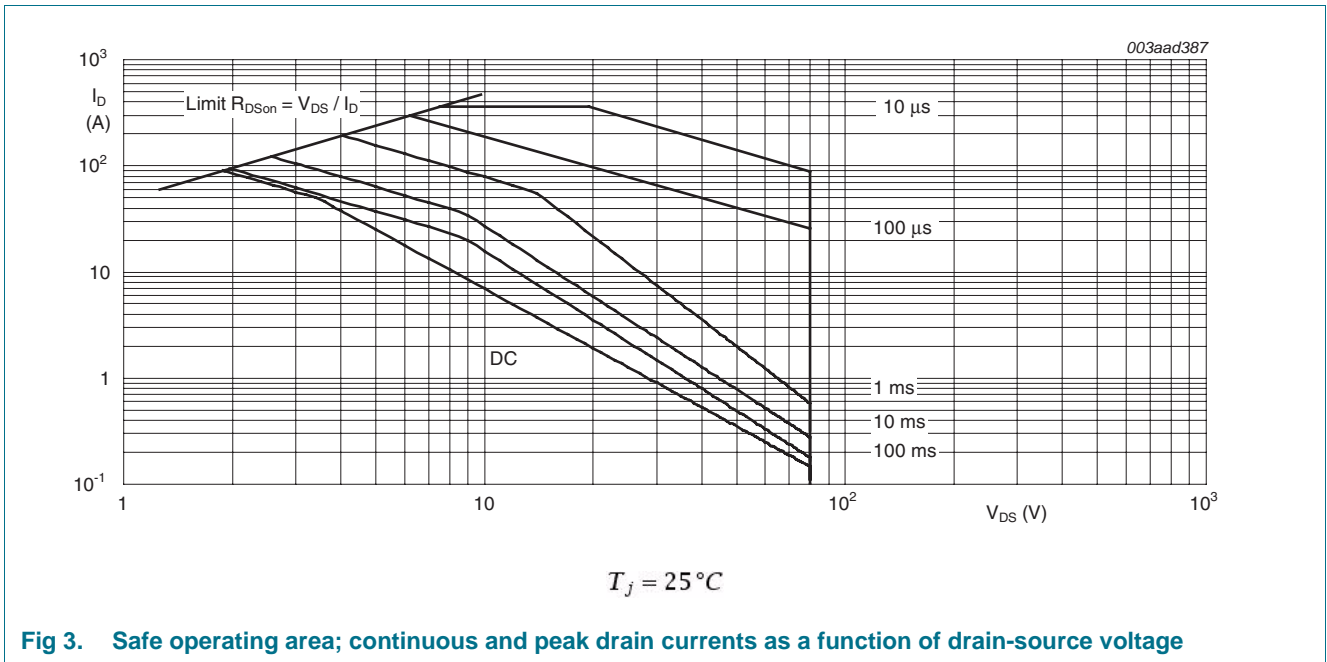
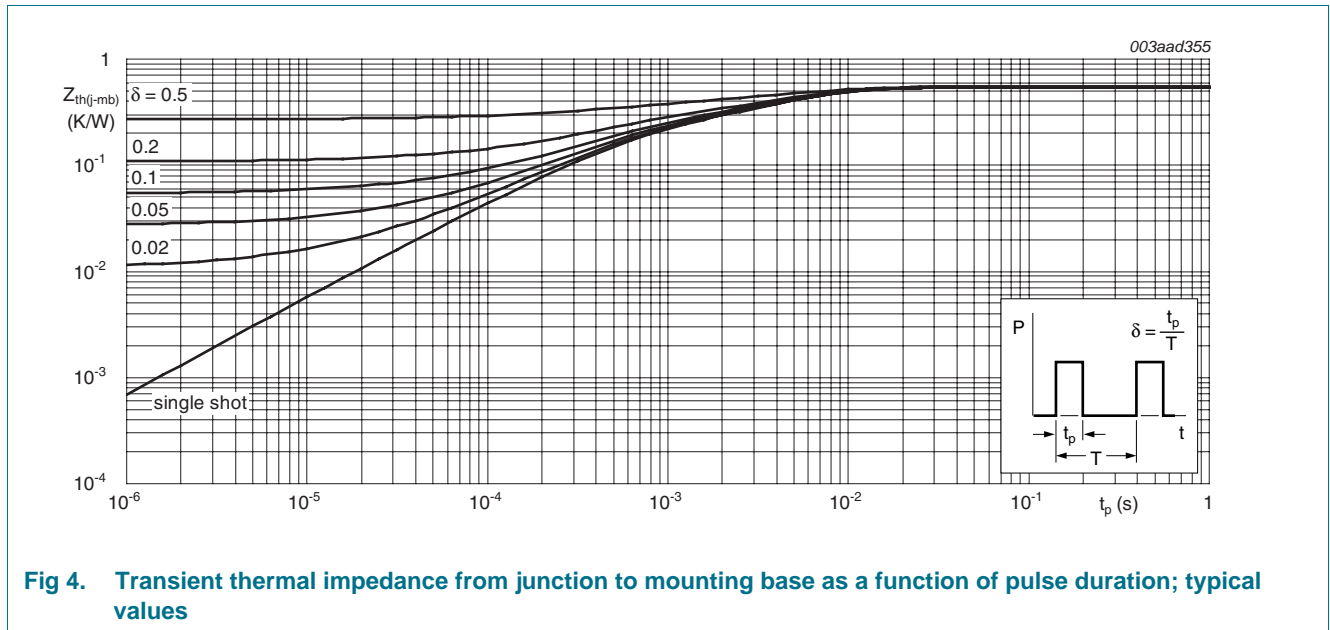


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.54	0.88	K/W



6. Characteristics

Table 6. Characteristics

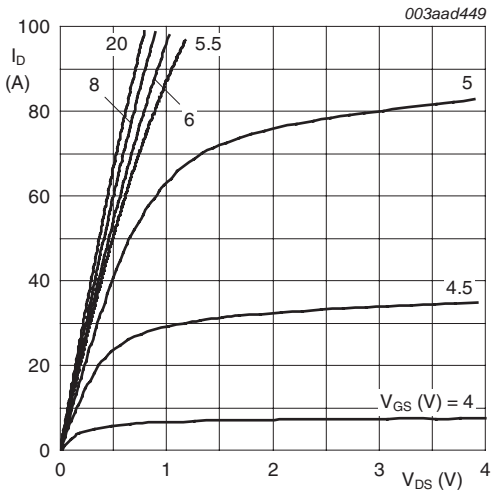
Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	73	-	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	80	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see Figure 10	1	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see Figure 10	-	-	4.6	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see Figure 11 ; see Figure 10	2.3	3	4	V
I _{DSS}	drain leakage current	V _{DS} = 80 V; V _{GS} = 0 V; T _j = 25 °C	-	0.3	5	μA
		V _{DS} = 80 V; V _{GS} = 0 V; T _j = 125 °C	-	-	100	μA
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 10 A; T _j = 175 °C; see Figure 12	-	-	20.8 8	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 100 °C; see Figure 12	-	-	14	mΩ
		V _{GS} = 10 V; I _D = 10 A; T _j = 25 °C; see Figure 13	U	-	7.5	8.7
R _G	internal gate resistance (AC)	f = 1 MHz	-	1	-	Ω
Dynamic characteristics						
Q _{G(tot)}	total gate charge	I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	44	-	nC
		I _D = 25 A; V _{DS} = 40 V; V _{GS} = 10 V; see Figure 14 ; see Figure 15	-	52	-	nC
Q _{GS}	gate-source charge		-	15	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	I _D = 25 A; V _{DS} = 40 V; V _{GS} = 10 V; see Figure 14	-	9.2	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	5.8	-	nC
Q _{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 40 V; V _{GS} = 10 V; see Figure 14 ; see Figure 15	-	11	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 40 V; see Figure 15	-	4.6	-	V
C _{iss}	input capacitance	V _{DS} = 40 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; see Figure 16	-	3346	-	pF
C _{oss}	output capacitance		-	296	-	pF
C _{rss}	reverse transfer capacitance		-	158	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 40 V; R _L = 1.6 Ω; V _{GS} = 10 V; R _{G(ext)} = 4.7 Ω	-	21	-	ns
t _r	rise time		-	26	-	ns
t _{d(off)}	turn-off delay time		-	46	-	ns
t _f	fall time		-	20	-	ns
Source-drain diode						
V _{SD}	source-drain voltage	I _S = 10 A; V _{GS} = 0 V; T _j = 25 °C; see Figure 17	-	0.79	1.2	V

Table 6. Characteristics ...continued
 Tested to JEDEC standards where applicable.

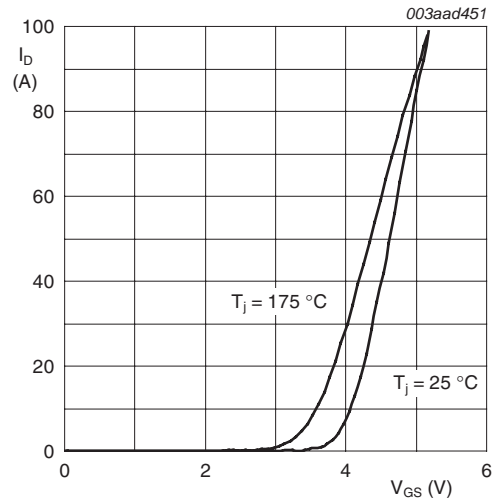
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $di_S/dt = 100 \text{ A}/\mu\text{s}$; $V_{GS} = 0 \text{ V}$; $V_{DS} = 40 \text{ V}$	-	42	-	ns
Q_r	recovered charge		-	66	-	nC

[1] Measured 3 mm from package.



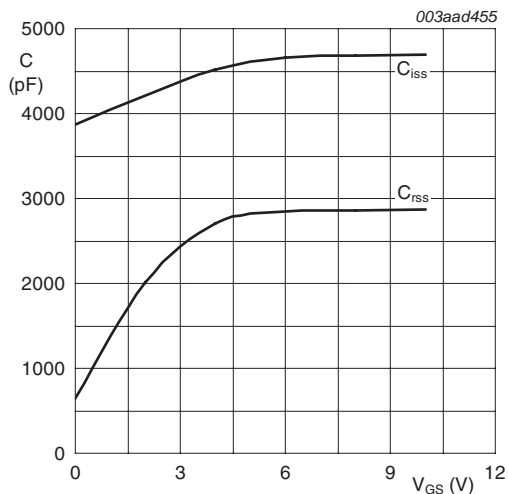
$T_j = 25^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



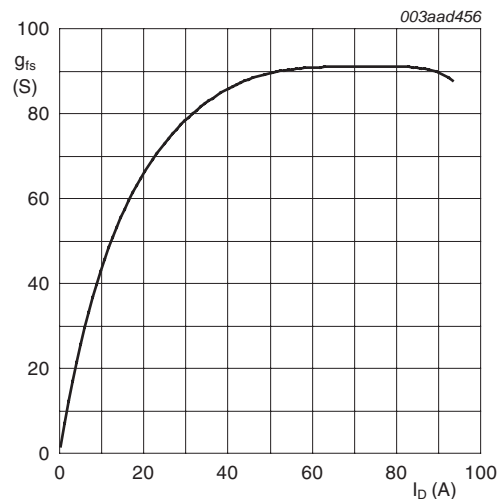
$V_{DS} > I_D \times R_{DS(on)}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



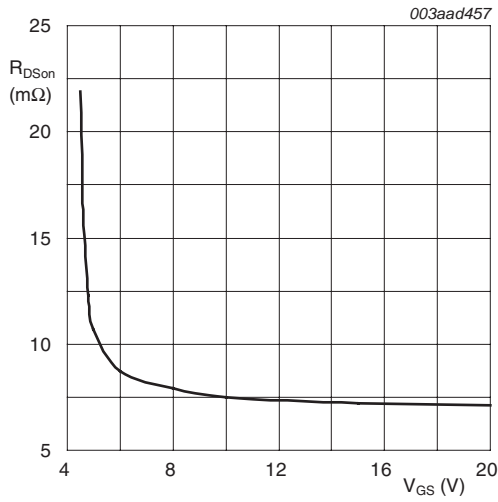
$V_{DS} = 0 \text{ V}$; $f = 1 \text{ MHz}$

Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



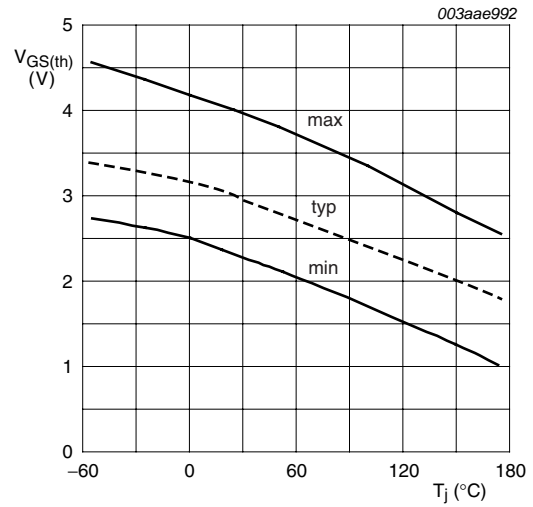
$T_j = 25^\circ\text{C}$; $V_{DS} = 15 \text{ V}$

Fig 8. Forward transconductance as a function of drain current; typical values



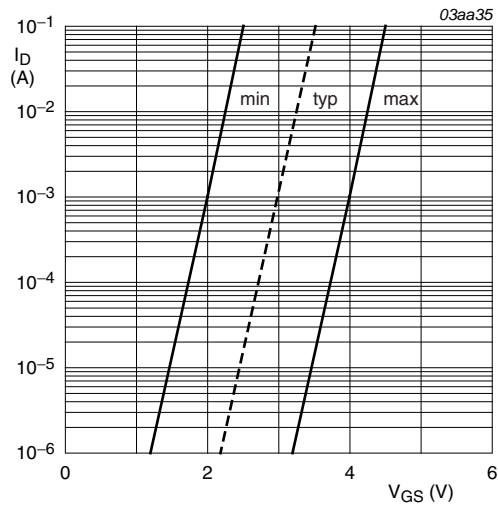
$T_j = 25^\circ C; I_D = 25A$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



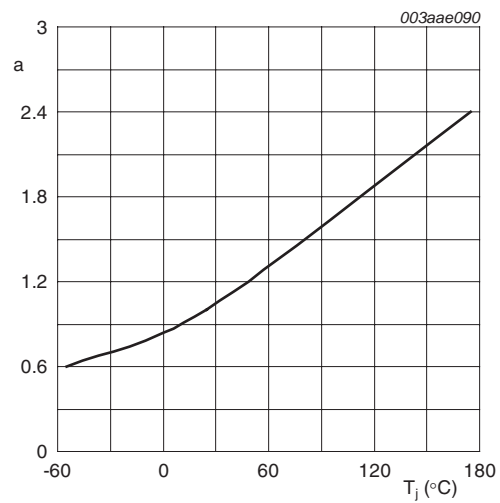
$I_D = 1 mA; V_{DS} = V_{GS}$

Fig 10. Gate-source threshold voltage as a function of junction temperature



$T_j = 25^\circ C; V_{DS} = 5V$

Fig 11. Sub-threshold drain current as a function of gate-source voltage



$$a = \frac{R_{DS(on)}}{R_{DS(on)@25^\circ C}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

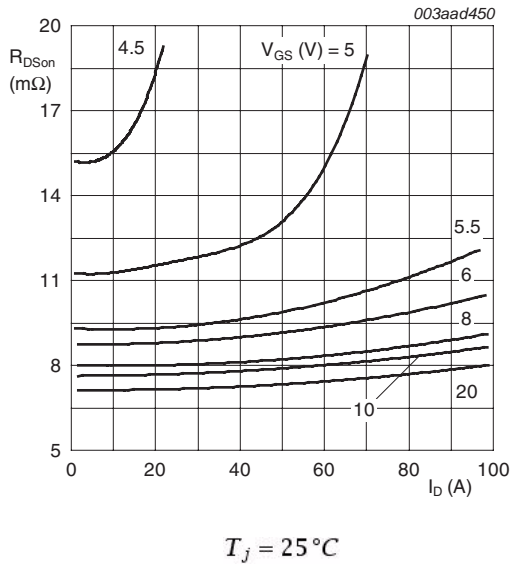


Fig 13. Drain-source on-state resistance as a function of drain current; typical values

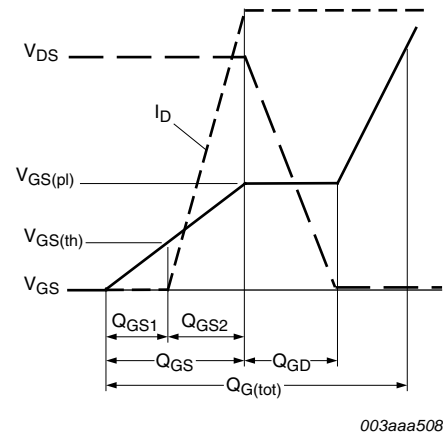


Fig 14. Gate charge waveform definitions

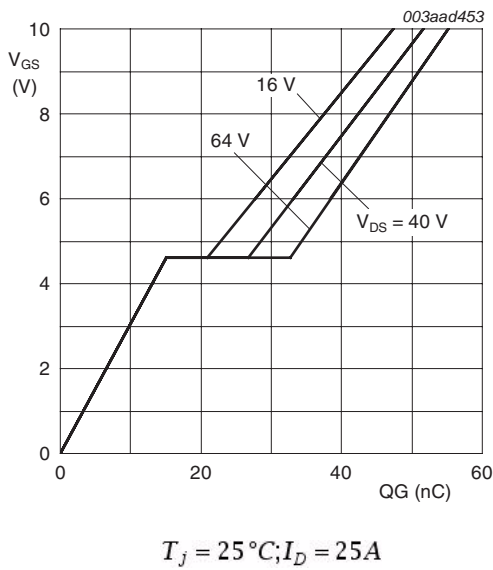


Fig 15. Gate-source voltage as a function of gate charge; typical values

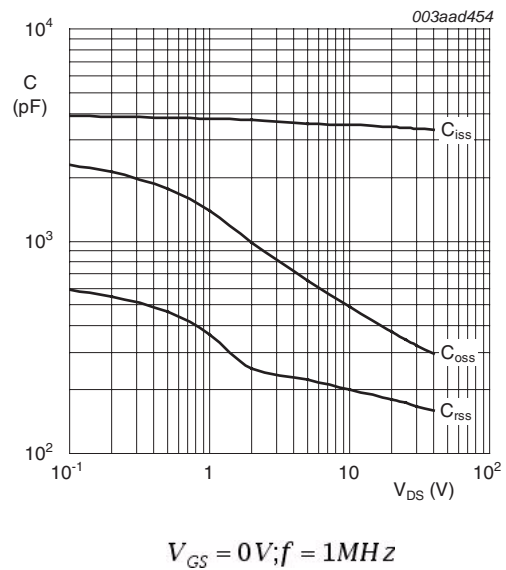


Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

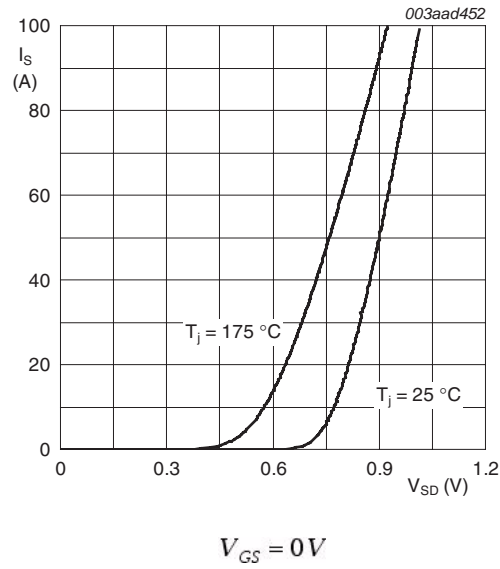


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

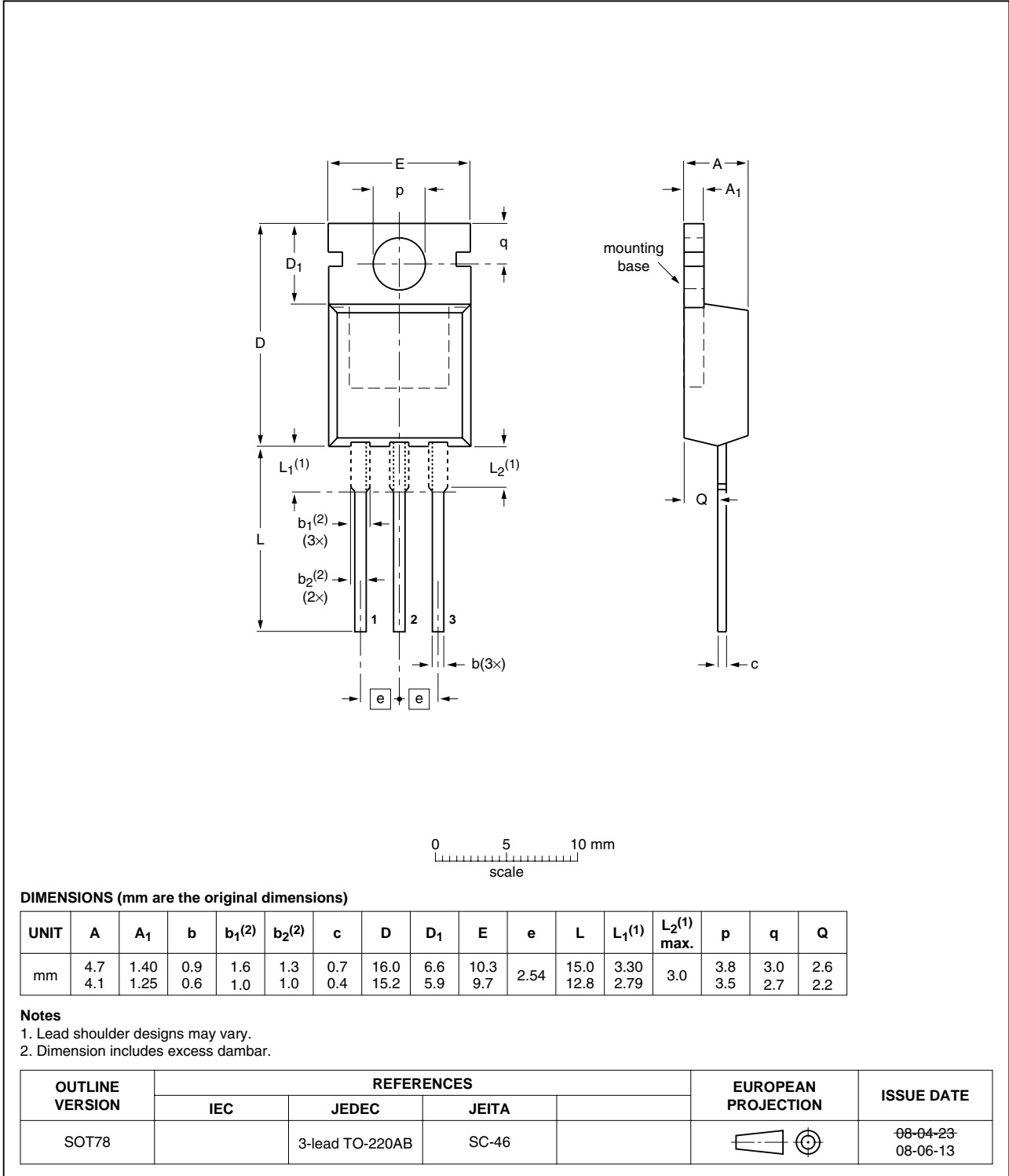


Fig 18. Package outline SOT78 (TO-220AB)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN8R7-80PS v.2	20101101	Product data sheet	-	PSMN8R7-80PS v.1
Modifications:	<ul style="list-style-type: none">• Status changed from objective to product.• Various changes to content.			
PSMN8R7-80PS v.1	20100129	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Contact Us :

➤ Address :

401 Building No.5, JiuGe Business Center, Lane 2301, Yishan Rd
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➤ Sales :

Direct +86 (21) 6401-6692

Email amall@ameya360.com

QQ 800077892

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➤ Customer Service :

Email service@ameya360.com

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Tel +86 (21) 64016692-8333

Email mkt@ameya360.com